746 T	TANTA UNIVERSITY FACULTY OF SCIENCE				
		DEPARTMENT OF PHYSICS			
	EXAM	EXAMINATION FOR SENIORS (FOURTH YEAR) STUDENTS OF MATERIAL SCIENCE			
	COURSE TITLE:	ELECTRON MICROSCOPY		COURSE CODE: MS4123	
DATE:	23\12\2017	TERM: FIRST	TOTAL ASSESSMENT MARKS:100	TIME ALLOWED: 2 HOURS	

## **ANSWER THE FOLLOWING QUESTIONS:**

Q1	( <u>25 Marks</u> )		
Writ	e about:		
a)	Mass-thickness contrast in TEM.		(10 Marks)
b	Electro-polishing and mechanical polishing	; in TEM.	(10 Marks)
<b>c</b> )	Importance of vacuum in electron microsco	рру.	(5 Marks)
Q2 (	( <u>25 Marks</u> )	••••••	••••••
a)	What are the possible processes that might l	happen when an energe	tic electron
	beam interacts with a solid? Enhance your a		(10Marks)
<b>b</b> )	Write about X-ray wavelength-dispersive sp	_	
	What are the disadvantages of TEM	17	(5 Marks)
b	List the possible defects of electron lenses a		(10 Marks) one of them? (10 Marks)
Q4- (	Choose the correct answer	( <u>30 Marks, 3 mark</u>	s each)
1)	A scanning electron microscope uses to prod	luce an image.	
	<ul><li>A) Negatively charged particles</li><li>C) Atoms</li></ul>	<ul><li>B) Positive charged par</li><li>D) Neutral particlee</li></ul>	ticle
2)	Increasing the accelerating voltage in TEM leads to A) A reduction in the scattering cross section of ele B) An increase in the electron wavelength C) A reduction in spatial resolution D) A reduction of penetration depth in the sample	ectrons	

وحدة ضمان الجودة © كالمناة خلف الصفحة كلية العلوم - جامعة علنما المناقل فاقى الأسئلة خلف الصفحة المناقلة المناقلة المناقلة و GUALITY ASSURANCE UNIT و FACULTY OF SCIENCE - TU

جامعة طنطا كرو مو رد دم كلية العلوم و الفيزياء

الزمن: ساعتان

## Answer the following:

- 1- How do you determine the crystal structure of BaTio3 ceramic?
- 2- How do you estimate the lattice parameters of the cubic and tetragonal unit cell?
- 3- Explain the hysteresis loop of BaTio3 ceramic.
- 4- Write a short note about the thermal conductivity of ceramic.



[10Marks]

200 <b>x</b>	TANTA UNIVERSITY- Faculty of Science -Department of Physics					
	EXAM FOR SENIORS STUDENTS OF MATERIALS SCIENCE					
	COURSE TITLE Mater		Materials Design	COURSE CODE: MS4121		
DATE:	30- 12 - 2017	TERM: FIRST	TOTAL ASSESSMENT MARKS: 100	TIME ALLOWED 2	HOURS	
First Que	estion:					
1- List th	e thermal protec	tion system de	esign requirements.		[15Marks	
2- Write	short notes abou	it material sele	ection for integrated circuit pack	kages.	[15Marks	
Second C	Question:					
1- Discus 2- Mentio	ss the <b>biocompa</b> on the required <b>r</b>	tibility during nechanical pr	the Artificial Total Hip Replace operties of the hip joint replaced	ment. d components.	[10Marks] [10Marks]	
Third Qu	<u>iestion:</u>				[30Marks	
1- The su	accessful operati	ion of the Spa	ce Shuttle is dependent on-1-		, tha	
			ecupants from $-2$			
			th's atmosphere.		+ ,	
•	•		reusable surface insulation (FF	RSI) is employed	on the Space	
			from -3 to - 4 -			
			<del>-</del> <del>-</del>			
			the artificial hip-6	7		
				<b>,</b> ,		
			and -11			
— — ar			leses where the principal disadva			
_ <del>_</del>						
for the	second is -13	<del></del>		<del></del>	_ <del></del> .	
5- Acetab	oular Cup cons	ists of -14	<b></b>	<del></del> -		
insert	that fits within	the cup; this	s cup is fabricated from-15 -			
			onded to the pelvis.			
Forth Qu	•					
Helical sp	pring of length		deflaction $(\theta)$ , cross section dia on by torque $(T)$ , find	ameter (d), modu	lus of rigidit	
					[10Marks]	
1- 1110 511	stiffness of the spring $(\frac{F}{8})$ , $\delta$ is axial deflection of spring. [10Marks]					

EXAMINER

2- Yield strength of spring.

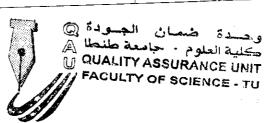
ڪلية العلوم - BEST WISHES - كالية العلوم - QUALITY ASSURANCE UNIT

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		<b>J</b> .)	· ·		
		TANTA UNIVERSITY FACULTY OF SCIENCE DEPARTMENT OF PHYSICS			
EXAMINATION FOR SENIORS (FORTH LEVEL) STUDENTS OF MATERIAL SCIENCE (SEMES)					
	000				
COURSE TITLE: DATE:1 JANUARY 2018	TERM: SUMMER	TOTAL ASSESSMENT MARKS: 100	TIME ALLOWED: 2 HOURS		
First question:	Ans	swer The Following:	{25 Marks} (12 Marks)		
·	erials. 2- Bulk	materials. 3- Grain size. 4- qua	•		
B) What are the advange and nanotechnology and n	ntages of using nicrotechnology	(nanomaterials comparing to b v.	(13 Marks)		
Second question:			{25 Marks}		
A) Write short not The unique size	tes on the follov e-dependent pr	ving: operties of nanomaterial (give e	(10 Marks) examples).		
B) Discuss the fab an example), d	orication metho eclare your ans	ds (top down-bottom up) of the wer by drawing.	nanomaterials; (give (15 Marks)		
Third question:			{20 Marks}		
A) Discuss briefly	the methods fo	or characterization of nanomate	erials. (10 Marks)		
B) Discuss the ap	plication of nar	nomaterials in (Information and	l communications). (10 Marks)		
Fourth question: Discuss and s	how the advant	age of using nanotechnology of	{30 Marks} the following fields:		
a) Diseases treat			(10 Marks)		
b) Environment			(10 Marks)		
		*			

C) Clean Energy.

Examiners Prof. Talaat M. Meaz Prof. Samia Saafan



(10 Marks)





#### **TANTA UNIVERSITY** FACULTY OF SCIENCE CHEMISTRY DEPARTMENT

#### FINAL EXAM FOR SENIOR STUDENTS (CHEMISTRY SECTION)

**COURSE** TITLE:

INDUSTRIAL CHEMISTRY (CH4123)

TIME ALLOWED:

DATE: JANUARY 06, 2018

TERM: **FIRST** 

TOTAL ASSESSMENT **MARKS: 100** 

2 HOURS

**Answer the Following Questions:-**

#### 1-(a)- Define each of the following terms:-

(6 Marks)

(Crude oil – Penicillin – LPG - Drying oils - Natural gas- Octane number)

#### (b)- Briefly discuss:-

(12 Marks)

- i) Properties of detergents.
- ii) The non-hydrocarbon compounds in petroleum.
- iii) Aromatic products and Chemical reactions carried out on benzene.

## 2-(a) Use the chemical equations to describe the following:-

(20 Marks)

- i) Manufacture of alpha-eucaine.
- ii) Synthesis of Tramadol.
- iii)Fries rearrangement of phenolic esters.
- iv) Synthesis of Piperocaine.

### (b)- Compare between:-

(12 Marks)

- i) Mordant and Reactive dyes with examples.
- ii) Gasoline and Diesel Oil.
- iii) Acid and Basic dyes with examples.

#### 3-(a) Write the Manufacture equations for:

(4Marks)

- i) POX for H<sub>2</sub> production
- ii) H<sub>2</sub>O<sub>2</sub>

## (b) Give reasons for the following statements:

(20Marks)

- i) White phosphorous used in military.
- ii) Addition of V<sub>2</sub>O<sub>5</sub> catalyst in manufacture of H<sub>2</sub>SO<sub>4</sub>.
- iii) Graphite is a low density.
- iv) Using carbon in manufacture of white phosphorus.

Please turn over





Date

# Tanta University Faculty of Science Physics Department



 First Term Exam (Level 4, Materials Science)		
Course Title	Microprocessing of Materials	Course Code: MS4131
11 / 1 / 2018	Total Assessment: 100 Marks	Time Allowed: 2 hours

## Please answer all the following questions:

#### First question: { 25 Marks }

- 1- Compare briefly between 3 different techniques for a thin film deposition. (15 Marks)
- 2- Show graphically only the working principles of (a) the focus ion beam (FIB) milling and (b) electron beam (EB) lithography as methods for nanofabrication. (10 Marks)

#### Second question: { 30 Marks}

- 1- What we mean by nanoimprint lithography? Compare between thermal imprint and step-flash as two nanoimprint methods. (15 Marks)
- 2- Show graphically only the general sequence of processing steps for a typical photolithography process. (10 Marks)
- 3- Show graphically only the difference between positive and negative photoresists. (5 Marks)

#### Third question: { 30 Marks}

- 1- If you are requested to fabricate silicon V-grooves show two possible fabrication methods and declare the advantages and disadvantages of each method. (10 Marks)
- 2- In the fabrication process of Si micro/nano structures, is it necessary to expect and control the thickness of SiO<sub>2</sub>? Why? (10 Marks)
- 3- Describe graphically, the basic idea of plasma etching of silicon using carbon tetrafluoride (CF<sub>4</sub>) (10 Marks)

## Fourth question: { 15 Marks}

- 1- How you can predict the photoresist thickness and why it is important predict and control the photoresist thickness? (10 Marks)
- 2- Show graphically a method enables you to grow silicon nanowires on the surface of a silicon wafer. (5 Marks)

●金銀 With my best wishes, Examiner: Dr Salah E. El-Zohary ●金銀



# Tanta University Faculty of Science Physics Department



	First Term Exam (Level 4, Mate	erials Science)
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Date 11 / 1 / 2018 Total Assessment: 100 Marks Time Allowed: 2 hours

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1 7	TANTA UNIVERSITY- Faculty of Science - Department of Physics				
	EXAM FOR 4 <sup>TH</sup> YEAR STUDENTS				
JONS	COURSE TITLE:	TITLE: Detectors and Accelerator Physics		COURSE CODE: PH4163	
DATE:	14 JAN 2017	TERM: FIRST	TOTAL ASSESSMENT MARKS: 100	TIME ALLOWED: 2 HOURS	

#### Answer the following questions

## Question one (30 points)

**A-** If a proton has a total energy of 1 TeV, what is its value of  $\beta$ ? (Hint:  $m_p = 1.673 \times 10^{-30} \text{ g}$ )

# B- Put ( ) or (x) and then discuss why you choose your answer:

- 1- The detector efficiency can be classified into two types of efficiency
- 2- The advantage of ionization chamber detectors is their dead time
- 3- There are three possibilities for the wall effect in the BF<sub>3</sub> tube
- 4- The overall gain of a PM depends on the secondary emission factor  $\delta$  only
- 5- The linearity of a PM depends strongly on the type of dynode configuration and the current in the tube only.
- 6- A high capacitance and a high frequency reduce the current dependence in the Cockcroft-Walton generator
- 7- Cyclotron is reasonable for accelerating electrons to high energies
- 8- In Betatron, the maximum energy for electrons is 300 MeV
- 9- In synchrotrons, focusing magnets are used.
- 10- The advantage of SSB detectors is their sensitivity to light
- 11- The length of the tube is the same in Wideroe's tube

Please turn the page for the other questions